

IDS LIST OF REFERENCES UNDER 37 C.F.R. 1.98

Sheet 1 of 2

Application Number : 10/595,523

Filing Date : April 25, 2006

First Named Inventor : Masahiro Nakayama

Art Unit : 2895

Examiner Name : Jae Lee

Docket Number : 039.0071

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <input type="checkbox"/>
F1	JP-2003-101068-A		04-04-2003	Sanyo Electric		

Examiner Signature	/Jae Lee/	Date Considered	12/14/2009
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.L./

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NON PATENT DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <input type="checkbox"/>
	01	M. LESZCZYNSKI et al., "GaN Homoepitaxial Layers Grown by Metalorganic Chemical Vapor Deposition," Applied Physics Letters, August 30, 1999, pp. 1276-1278, Vol. 75, No. 9, American Institute of Physics, NY.	<input type="checkbox"/>

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